Central [™]	2N5875 2N5876 PNP 2N5877 2N5878 NPN
Semiconductor Corp. 145 Adams Avenue, Hauppauge, NY 11788 USA	COMPLEMENTARY SILICON POWER TRANSISTORS
Tel: (631) 435-1110 • Fax: (631) 435-1824 Manufacturers of World Class Discrete Semiconductors	JEDEC TO-3 CASE

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DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5875, 2N5877 series types are Complementary Silicon Power Transistors manufactured by the epitaxial base process mounted in a hermetically sealed metal case designed for general purpose switching and amplifier applications.

MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Collector-Base Voltage Collector-Emitter Voltage	SYMBOL VCBO VCEO	2N5875 <u>2N5877</u> 60 60	2N5876 <u>2N5878</u> 80 80	UNIT V V
Emitter-Base Voltage	VEBO	5.0		V
Collector Current	1 _C	10		А
Collector Current(PEAK)		20		А
Base Current		4.0		А
Power Dissipation Operating and Storage	PD	150	i .	W
Junction Temperature	T _J ,T _{stg}	-65 TO +	200	°C
Thermal Resistance	ΘJC	1.1	7	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

ELECTRICAL			875 877		876 878	
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNIT
ICEV	V_{CE} =Rated V_{CEO} , V_{BE} (OFF) 1.5V		0.5		0.5	mA
ICEV	V_{CE} =Rated V_{CEO} , $V_{BE}(OFF)=1.5V$, $T_{C}=150^{\circ}C$		5.0		5.0	mA
I CEO	$V_{CE} = \frac{1}{2}Rated V_{CEO}$		1.0		1.0	mΑ
ICBO	V _{CB} =Rated V _{CBO}		0.5		0.5	mA
FBO	V _{FB} =5.0V		1.0		1.0	mA
BVCEO	I _C ≈200mA	60		80		V
V _{CF} (SAT)	Ι _C =5.0A, Ι _B =0.5A		1.0		1.0	V
V _{CF} (SAT)	$I_{C} = 10A, I_{B} = 2.5A$		3.0		3.0	V
V _{BF} (SAT)	$I_{C} = 10A$, $I_{B} = 2.5A$		2.5		2.5	V
VBE(ON)	$V_{CE}^{=4.0V}$, $I_{C}^{=4.0A}$		1.5		1.5	V
hEE	$V_{CE}=4.0V, I_{C}=1.0A$	35		35		
hFE	$V_{CE}=4.0V, I_{C}=4.0A$	20	100	20	100	
hFE	$V_{CE}=4.0V$, $I_{C}=10A$	4.0		4.0		
hfe	V _{CE} =4.0V, I _C =1.0A, f=1.0kHz	20		20		
fT	$V_{CF}=10V$, $I_{C}=0.5A$, f=1.0MHz	4.0		4.0		MHz
Cob	V _{CB} =10V, I _E =0, f=1.0MHz (PNP TYPES)		500		500	pF
Cob	. V _{CB} =10V, I _c =0, f=1.0MHz (NPN TYPES)		300		300	pF
tr	$V_{CC}=30V$, $I_{C}=4.0A$, $I_{B1}=I_{B2}=0.4A$		0.7		0.7	μs
toff	$V_{CC}=30V$, $I_{C}=4.0A$, $I_{B1}=I_{B2}=0.4A$		1.8		1.8	μs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES

PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- · Environmental regulation compliance
- Customer specific screening
- · Up-screening capabilities

· Custom product packing

Custom bar coding for shipments

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

REQUESTING PRODUCT PLATING

- If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when 1. ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

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